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20 V, single N-channel Trench MOSFET 13 November 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT363 (SC-88) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	3.3	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 3 A; T _j = 25 °C		-	45	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





20 V, single N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	6 5 4	D
2	D	drain		
3	G	gate		G UT 4
4	S	source	∐1 ∐2 ∐3	S 017aaa253
5	D	drain	TSSOP6 (SOT363)	017444255
6	D	drain		

3. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
PMG45UN	TSSOP6	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMG45UN	U5%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

drain-source voltage	T _i = 25 °C				_
	J		-	20	V
gate-source voltage			-8	8	V
drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	3.3	А
	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	3	А
	V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	1.9	А
peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	12	А
total power dissipation	T _{amb} = 25 °C	[2]	-	375	mW
		[1]	-	715	mW
-	drain current peak drain current total power dissipation	$\begin{array}{c} V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 25 ^{\circ}\text{C}; \text{t} \leq 5 \text{ s} \\ \hline V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 25 ^{\circ}\text{C} \\ \hline V_{GS} = 4.5 \text{ V}; \text{T}_{amb} = 100 ^{\circ}\text{C} \\ \hline \text{Peak drain current} \\ \end{array}$	$\begin{array}{ c c c c c } \hline & & & & & & & & & & & & & & & & & & $	$ \begin{array}{c c} \mbox{drain current} & V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C; \ t \leq 5 \ s & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline peak \ drain \ current & T_{amb} = 25 \ ^{\circ}C; \ single \ pulse; \ t_p \leq 10 \ \mu s & - \\ \hline total \ power \ dissipation & T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline \hline 1 & - & \\ \hline \end{array} $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

PMG45UN

20 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Мах	Unit
		T _{sp} = 25 °C		-	4350	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	0.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

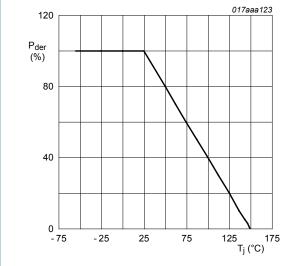


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

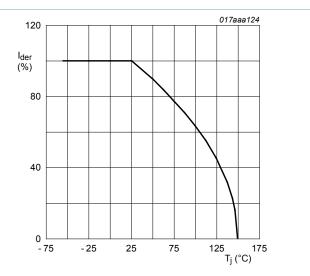
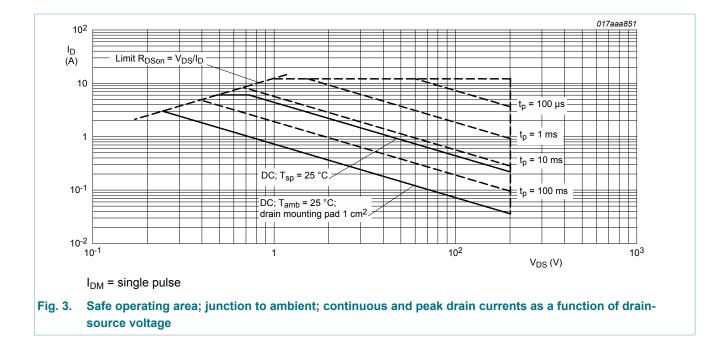


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

20 V, single N-channel Trench MOSFET



6. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance		in free air	[1]	-	289	332	K/W
from junction to ambient			[2]	-	152	175	K/W
ampient	ambient		[3]	-	117	145	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	29	K/W

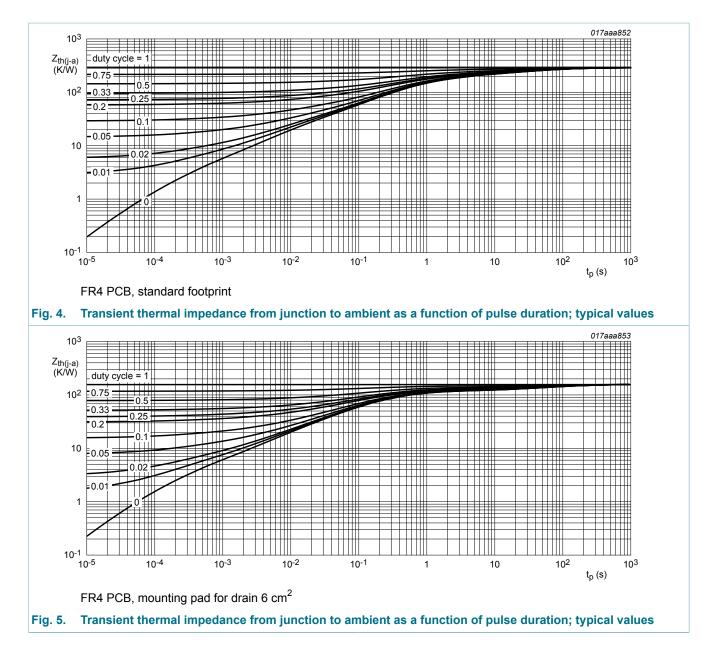
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t \leq 5 s.

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20 V, single N-channel Trench MOSFET



7. Characteristics

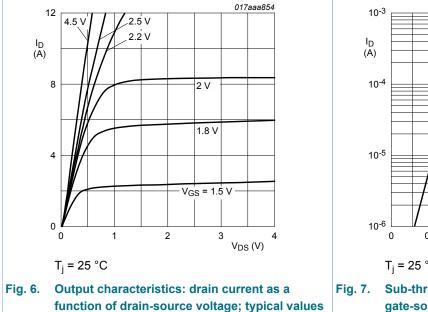
Table 7. C	haracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		20	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.4	0.7	1	V
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
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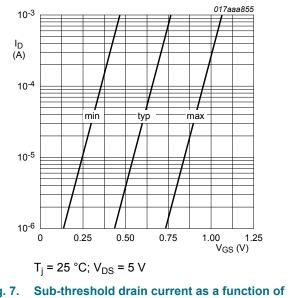
Product data sheet

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20 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 3 A; T _j = 25 °C	-	45	55	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 3 A; T _j = 150 °C	-	66	81	mΩ
		V _{GS} = 2.5 V; I _D = 2.5 A; T _j = 25 °C	-	58	76	mΩ
		V _{GS} = 1.8 V; I _D = 0.8 A; T _j = 25 °C	-	85	125	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 3 A; T _j = 25 °C	-	11.2	-	S
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I _D = 3 A; V _{GS} = 4.5 V;	-	2.2	3.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.32	-	nC
Q _{GD}	gate-drain charge		-	0.56	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	184	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	51	-	pF
C _{rss}	reverse transfer capacitance	_	-	29	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I _D = 3 A; V _{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	30	-	ns
t _{d(off)}	turn-off delay time		-	30	-	ns
t _f	fall time		-	26	-	ns
Source-dra	iin diode	·				
V _{SD}	source-drain voltage	I_{S} = 0.8 A; V_{GS} = 0 V; T_{j} = 25 °C	-	0.8	1.2	V

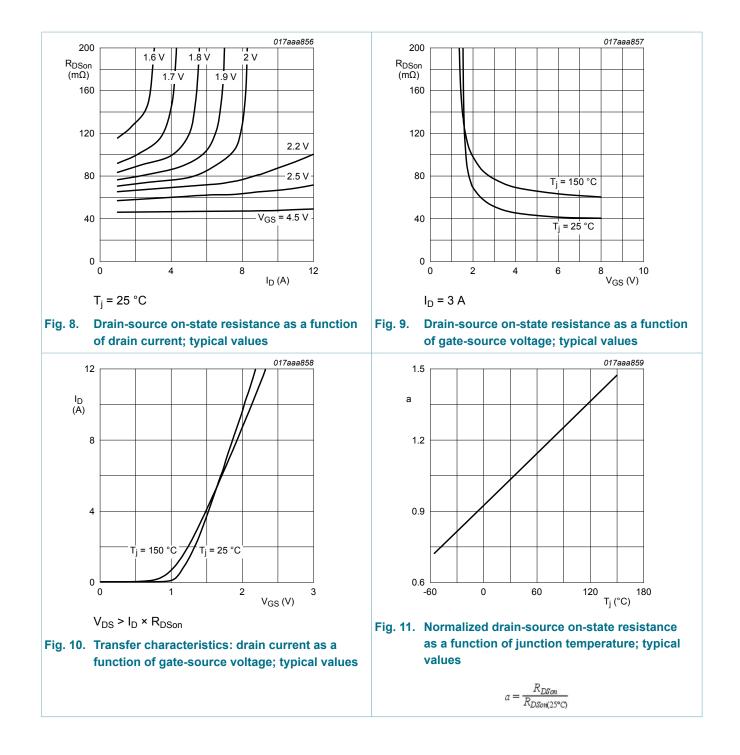




gate-source voltage

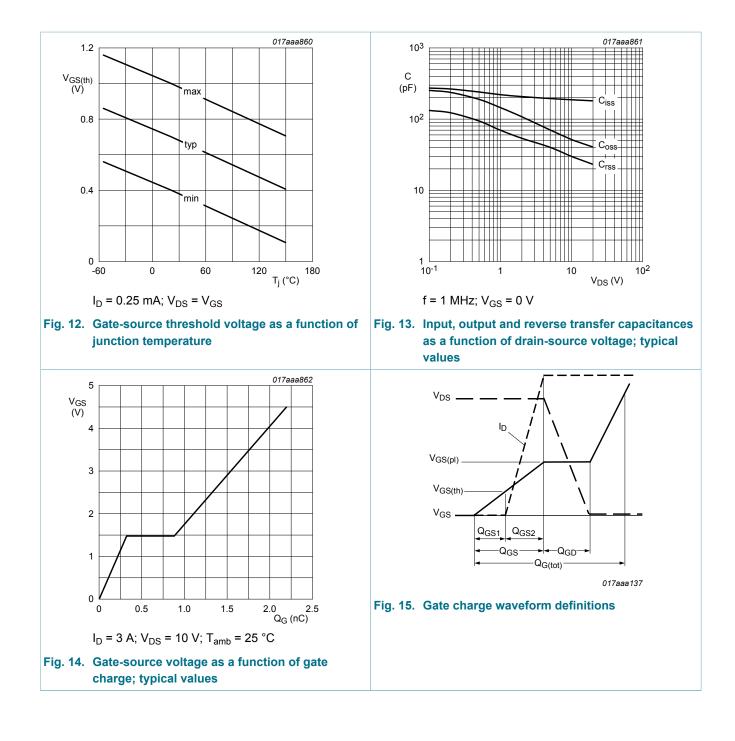
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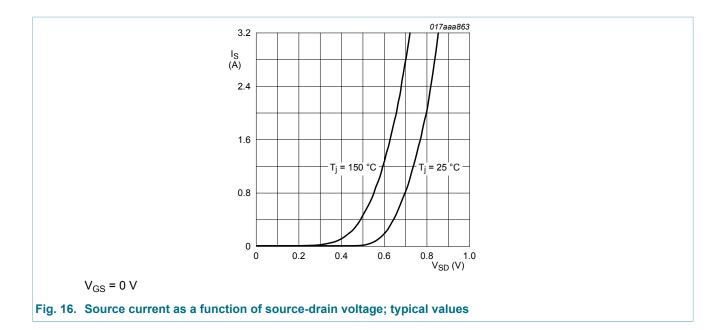
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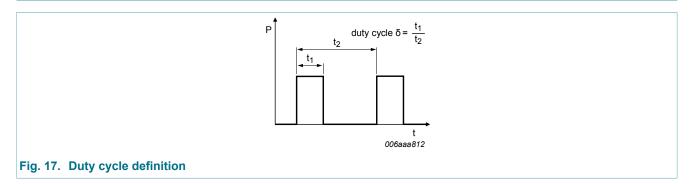


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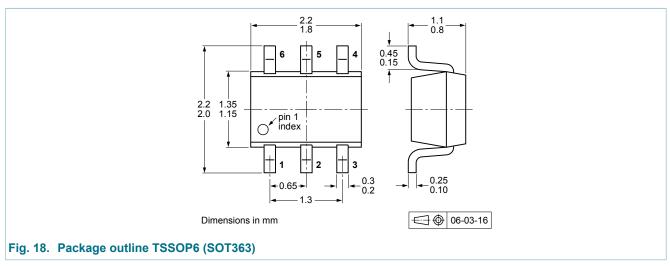
20 V, single N-channel Trench MOSFET



8. Test information

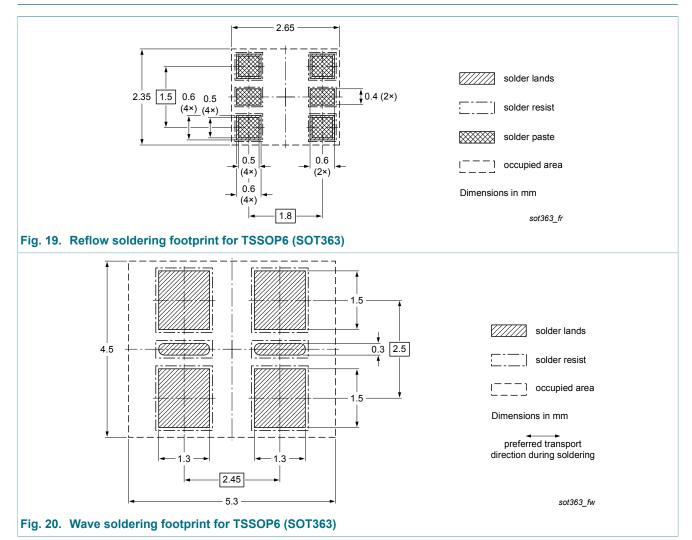


9. Package outline



20 V, single N-channel Trench MOSFET

10. Soldering



11. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMG45UN v.1	20121113	Product data sheet	-	-	

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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